Active Metamaterial Transmission Line with Gain in SiGe BiCMOS Technology

C. X. Zhou 1, Yihu Li 2, Y. Z. Xiong 2, and W. Wu 1

1 Ministerial Key Laboratory of JGMT
Nanjing University of Science and Technology, Nanjing, 210094, China
zhouchx1010@gmail.com, wuwen@mail.njust.edu.cn

2 Terahertz Research Center
CAEP, Chendu, 611731, China
yli2@e.ntu.edu.sg, eyzxiong@ieee.org

Abstract — We report the realization of an active composite right/left-handed (CRLH) metamaterial transmission line (TL) with gain. By employing the transistors in SiGe BiCMOS technology, an active CRLH TL has been realized exhibiting net gain, wide-band and flat S-parameter characteristics. Effective electromagnetic parameters of the active CRLH TL, including complex propagation constant γ, effective permittivity $\varepsilon_{\text{eff}}$, effective permeability $\mu_{\text{eff}}$ and index of refraction $n$ are extracted, which reveal the left handed properties of the active CRLH TL. The electric plasma frequency $f_{\text{pe}}$ and the magnetic plasma frequency $f_{\text{me}}$ are observed in the proposed TL.

Index Terms— Active, CRLH TL, metamaterial, SiGe BiCMOS.

I. INTRODUCTION

Metamaterials have special electromagnetic properties such as negative permittivity $\varepsilon$, negative permeability $\mu$ and negative index of refraction $n$, which are typically not observed in nature. Research on metamaterials has made great progress since experimental verification of negative index refraction [1] has been reported. Composite right-handed (CRLH) transmission line (TL) [2,3] and split ring resonators (SRRs) [4] are commonly two kinds of realization of metamaterials. However, the loss and narrow bandwidth inherently associated with the metamaterials are the main bottleneck that restrict their applications especially in high frequency. Active constituents, such as RF amplifier [5], gain medium rhodamine [6] and germanium tunnel diode [2] were adopted to alleviate the loss problem.

Silicon based SiGe CMOS technology is the most suitable platform for realization of the active CRLH TLs. Because it is available for producing various of active constituents such as transistors and diodes, and lumped elements such as inductance L and capacitance C. Also, it offers integration and small size which is a requirement as the unit length of the CRLH TL should be smaller than the wavelength. Thus, the operating frequency can be extended to microwave and millimeter-wave, even to terahertz (THz).

In this letter, an active CRLH TL with both gain and impedance matching in wideband is demonstrated. Effective electromagnetic parameters including transmission line complex propagation constant $\gamma$, effective permittivity $\varepsilon_{\text{eff}}$, effective permeability $\mu_{\text{eff}}$ and index of refraction $n$ are extracted to analyze the characteristics of the active CRLH TL. The electric plasma frequency $f_{\text{pe}}$ and the magnetic plasma frequency $f_{\text{me}}$ are observed, which defined as the transition frequency between the negative and positive value of $\varepsilon_{\text{eff}}$ and $\mu_{\text{eff}}$, respectively.

II. DESIGN OF THE ACTIVE CRLH TL

The schematic of the active CRLH TL is shown in Fig. 1 (a), which contains two distributed unit cells and matching circuits. When the input signal is supplied to the base of the HBT transistor in one unit cell, the amplified output signal can be obtained in the collector. The output signals from each unit cell sum in phase as the delays of the input and output lines are made equal. Terminating matching loads are used to minimize destructive reflections. Its equivalent circuit model of one unit cell of the active CRLH TL is shown in Fig. 1 (b). The passive part of the active CRLH TL unit cell in Fig. 1 (b) is similar to the classic CRLH TL theory [7], including a series connection of inductance $L_R$ and capacitance $C_L$ and a shunt connection inductance $L_L$ and capacitance $C_R$. They come from two parts: the lumped elements realized in Fig. 1 (a) and the parasitic effects of the HBT transistor. In this design, the designed values...
of the passive part are: \( L_R = 550.2 \text{ pH} \), \( L_L = 249.0 \text{ pH} \), \( C_R = 220.1 \text{ fF} \), \( C_L = 99.6 \text{ fF} \). Thus, the passive part is balanced at frequency:

\[
f_0 = f_a \left( 1/2 \pi \sqrt{L_R C_L} \right) = f_a \left( 1/2 \pi \sqrt{L_L C_R} \right) = 21.5 \text{ GHz}.
\]

The active part of one unit cell in Fig. 1 (b) is an amplifier unit which provides a voltage-controlled current source to the traditional CRLH TL. It is used to not only compensate the loss from the lumped elements, but also providing gain to the CRLH TL.

Considering the parasitic effects of the transistors, the designed parameters in Fig. 1 (a) are \( L_{R1} = L_{R2} = 500 \text{ pH} \), \( L_{L1} = L_{L2} = 406 \text{ pH} \), \( C_{R1} = C_{R2} = 148 \text{ fF} \), \( C_{L1} = C_{L2} = 162.4 \text{ fF} \).

The simulated and measured S parameters are shown in Fig. 2. The measured gain of the active CRLH TL is about 10.5 dB from 10.7 GHz to 31 GHz with \( \pm 1 \text{ dB} \) ripple and good impedance matching can be observed in this band. Compared with other kinds of CRLH, the proposed CRLH TL in this paper has net gain, wideband, and flat S-parameter characteristics. The left-handed properties of CRLH TL will be discussed by extraction of effective electromagnetic parameters in the following section.

\[\begin{align*}
\text{Effective electromagnetic parameters of passive metamaterials can be extracted from measured two-port S-parameters by Nicolson-Ross-Weir (NRW) approach [8-10]. In this method, the choice of sign of the transmission factor \( T \) and reflection factor \( \Gamma \) is determined by \( |\Gamma| \leq 1, |T| \leq 1 \). While for active metamaterials TL with gain in this design, the constraint is modified to \( |\Gamma| \leq 1 \). With this method, the complex propagation constant \( \gamma = \alpha + j\beta \) (\( \alpha \) is the propagation attenuation constant and \( \beta \) is the phase constant), effective permittivity \( \varepsilon_{\text{eff}} \), effective permeability \( \mu_{\text{eff}} \) and index of refraction \( n \) are shown in Fig. 3. From Fig. 3 (a), the negative \( \beta \) from 0 GHz to 19.5 GHz is observed. Thus, the TL exhibits left-handed property below 19.5 GHz and right-handed property above 19.5 GHz. This frequency is shifted downward compared with the designed frequency 21.5 GHz, which could be caused by the inaccuracy of the parameter extraction of the transistors and interconnects. Also, we can obtain negative \( \alpha \) from 5 GHz to 57.5 GHz, which means that the magnitude of \( S21 \) is larger than 0 dB in this range.
\end{align*}\]

For further insight into the electromagnetic properties of the CRLH TL, the corresponding index of refraction \( n \) is calculated and plotted in Fig. 3 (c). The inset shows the details of the original graph near zero-Y-axis. The real part of \( \mu_{\text{eff}} \) is negative below 19.3 GHz and from 2.8 GHz to 19.5 GHz the real part of \( \varepsilon_{\text{eff}} \) is negative, which verify the left-handed properties below 19.5 GHz. Thus, the electric plasma frequency \( f_{pe} \) and the magnetic plasma frequency \( f_{mu} \) is 19.3 GHz and 19.5 GHz, respectively. Below 3.4 GHz and above 7.2 GHz, the imaginary part of \( \mu_{\text{eff}} \) is positive and from 3.4 GHz to 41.7 GHz, the imaginary part of \( \varepsilon_{\text{eff}} \) is positive, which account for the gain properties of the TL.

\[\begin{align*}
\text{Fig. 1 (a) Schematic of the active CRLH TL. (b) The equivalent circuit model of one unit cell.}
\end{align*}\]
original graph near zero-Y-axis. The real part of \( n \) is negative below 19.5 GHz, which indicates left-handed property of the CRLH TL in this band. From 5 GHz to 57.5 GHz, the imaginary part of \( n \) are negative, indicating the gain property of the CRLH TL.

![Fig. 3](image)

**Fig. 3.** (a) Extracted complex propagation constant \( \gamma(\alpha+j\beta) \) from measured two-port S-parameter. (b) Extracted effective permittivity \( \varepsilon_{\text{eff}} \) (red) and effective permeability \( \mu_{\text{eff}} \) (blue) from measured two-port S-parameter. The inset shows the details near zero-Y-axis. (c) Extracted index of refraction \( n \) from measured two-port S-parameter. The inset shows the details near zero-Y-axis.

## IV. CONCLUSION

In conclusion, we present an active CRLH TL based on BiCMOS technology. Improved performances were experimentally demonstrated in terms of high gain, wideband impedance matching and flat S-parameter characteristics. Effective electromagnetic parameters of the active CRLH TL are analyzed, which can be the basis to the design and application of active metamaterials. Potential applications of the proposed CRLH TL can be foreseen in filters, amplifiers, phase shifters etc.

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**REFERENCES**


Chun-Xia Zhou (M’14) was born in Jiangsu Province, China, in 1985. She received the B.S. and Ph.D. degree in Electronic Engineering from Nankai University, Tianjin, China, in 2007 and 2012, respectively. From September 2010 to February 2012, she was a joint Ph.D. student with the Department of Electrical and Computer Engineering, National University of Singapore (NUS), Singapore. From December 2012 to July 2012, she was a Research Fellow with Terahertz Science and Technology Research Center of China Academy of Engineering Physics, Chengdu, China. She is currently a Lecturer with the School of Electronic Engineering and Optoelectronic Technology, Nanjing University of Science and Technology, Nanjing, China. Her research interests include the design and optimization of microwave and millimeter-wave circuits, and microwave and millimeter-wave integrated circuits in CMOS technology.

Yihu Li received the B.S. degree in Electrical and Electronic Engineering from Nanyang Technological University, Singapore, in 2010, where he is currently working towards the Ph.D. degree in Electrical and Electronic Engineering. He is currently attached to the Semiconductor Device Research Laboratory, China Academy of Engineering Physics.

Yong-Zhong Xiong (M’98–SM’02) received the B.S. and M.Eng. degrees in Communication and Electronic Systems from Nanjing University of Science and Technology, Nanjing, China, in 1986 and 1990, respectively, and the Ph.D. degree in Electrical and Electronic Engineering from Nanyang Technological University, Singapore. From 1986 to 1994, he was with the Department of Electronic Engineering, Nanjing University of Science and Technology, Nanjing, China, where he was involved with microwave systems and circuit design. In 1994, he was a Research Scholar with Nanyang Technological University (NTU), Singapore. From 1995 to 1997, he was a Senior Engineer with the RF and Radios Department, Singapore Technologies. He was with the Microelectronics Center, NTU. Since September 2001, he was with the Institute of Micro-electronics, Agency for Science, Technology and Research, Singapore. He is currently a Professor and Director of the Semiconductor Device Research Laboratory, China Academy of Engineering Physics. He has authored or co-authored over 180 technical papers. His leading research areas include silicon-based monolithic integrated-circuit design and characterization for millimeter wave and terahertz applications and device RF and noise modeling and characterization.

Wen Wu(SM’10) received the Ph.D. degree in Electromagnetic Field and Microwave Technology from Southeast University, Nanjing, China, in 1997. He is currently a Professor with the School of Electronic Engineering and Optoelectronic Technology and an Associate Director with the Ministerial Key Laboratory of JGMT, Nanjing University of Science and Technology, Nanjing, China.

Wu has authored and co-authored over 120 journal and conference papers. He has submitted five patent applications. His current research interests include microwave and millimeter-wave (mm-wave) theories and technologies, microwave and mm-wave detection, and multimode compound detection. Wu was a six-time recipient of the Ministerial and Provincial-Level Science and Technology Award.